

1. General description

Planar passivated three quadrant guaranteed commutation triac in a SOT223 surface mountable plastic package for use in motor control circuits or with other highly inductive loads. This triac balances the requirements of commutation performance and gate sensitivity and is intended for use with low power drivers, including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt with sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package

3. Applications

- General purpose motor controls
- Small loads in washing machines
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

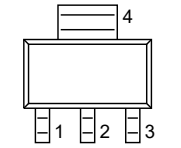
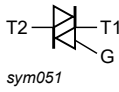
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	11	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	10	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 9	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	10	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 11	-	-	12	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12	-	0.7	1.5	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ °C}$; (67% of V_{DRM}); exponential waveform; gate open circuit	30	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 1\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	2	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>SC-73 (SOT223)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
4	mb	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
T204W-800E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Limiting values

Table 4. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	11	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	10	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.5	A ² s
dl_T/dt	rate of rise of on-state current	$I_G = 0.2\text{ A}$	-	100	A/ μ s
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	125	°C

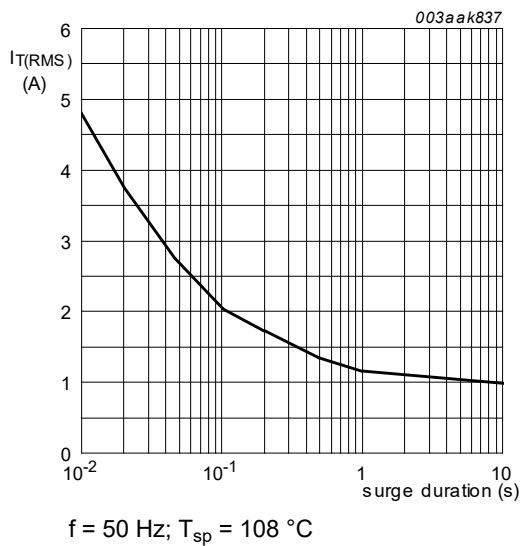


Fig. 1. RMS on-state current as a function of surge duration; maximum values

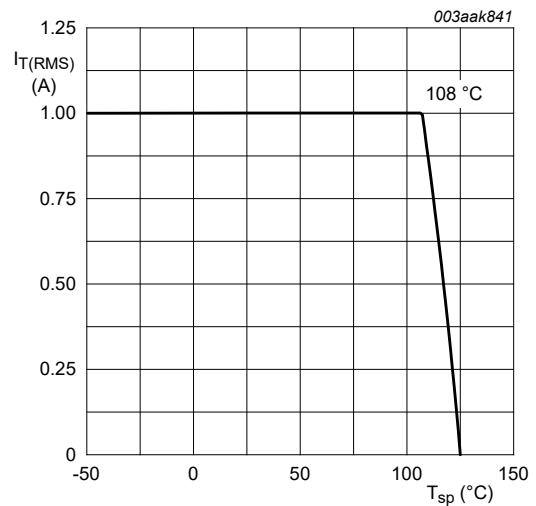


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

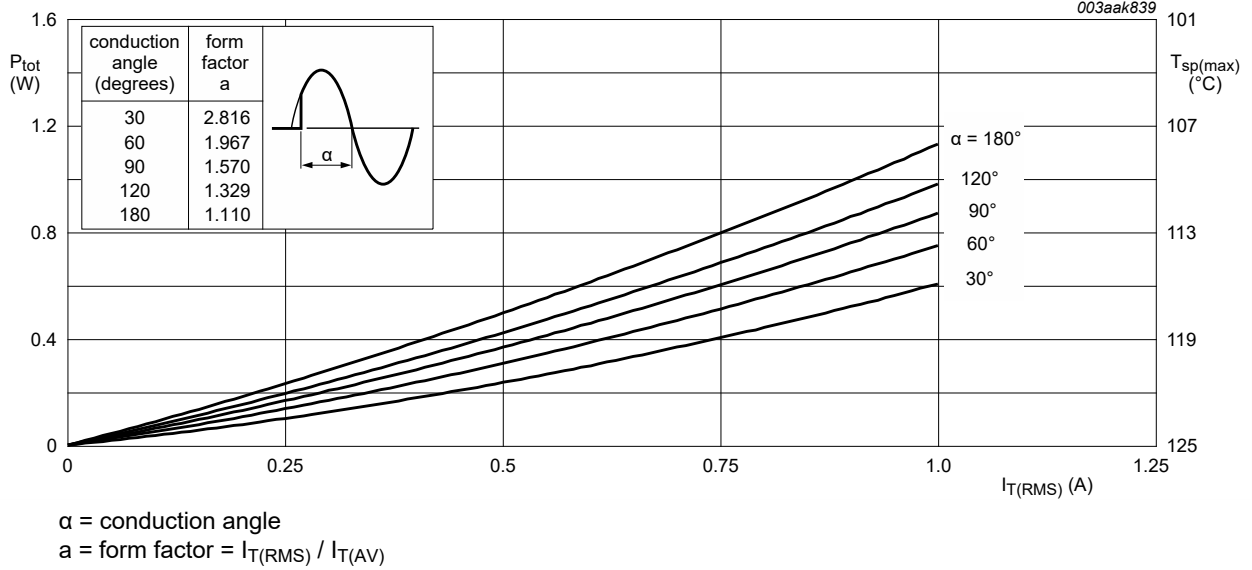


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

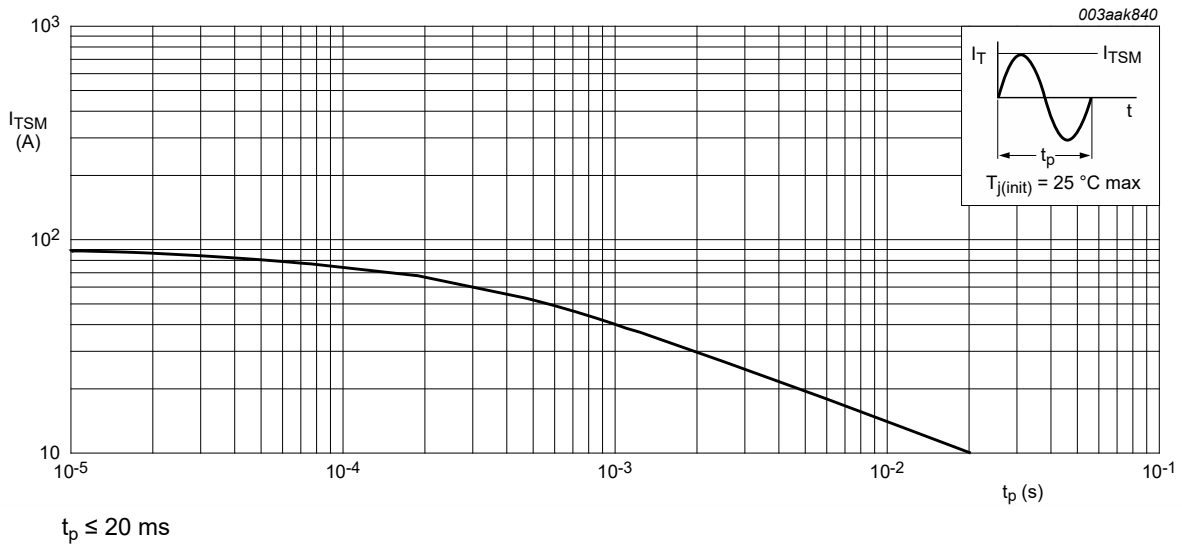
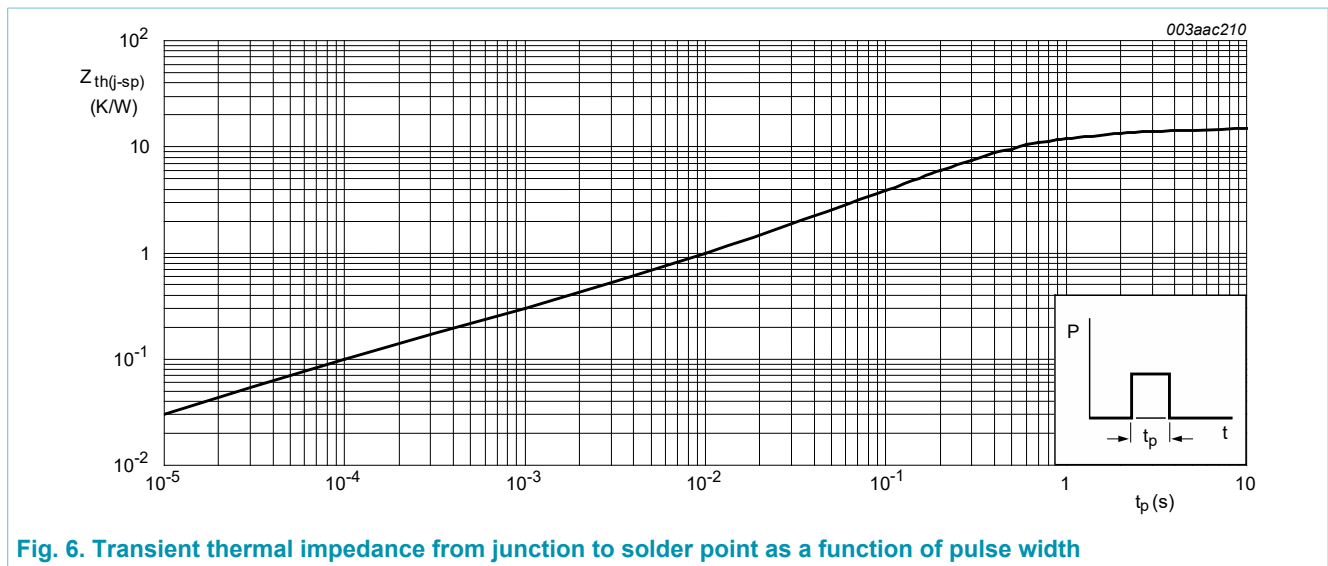


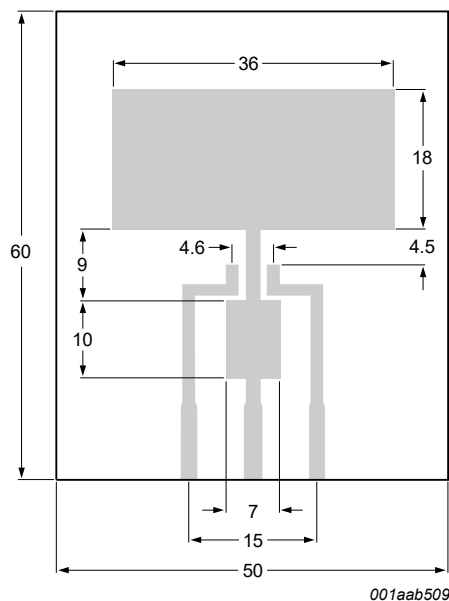
Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

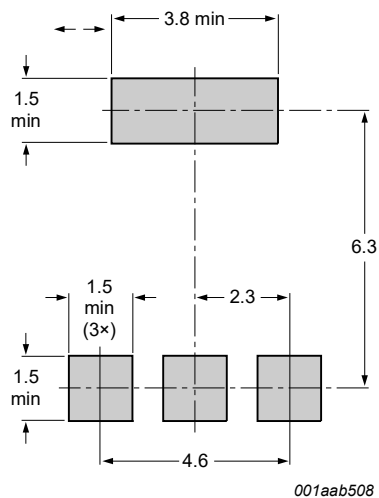
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle or half cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air; printed circuit board mounted: minimum pad area; Fig. 7	-	70	-	K/W
		in free air; printed circuit board mounted: minimum footprint; Fig. 8	-	156	-	K/W





All dimensions are in mm
Printed circuit board:
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 um thick)

Fig. 7. Printed circuit board pad area: SOT223



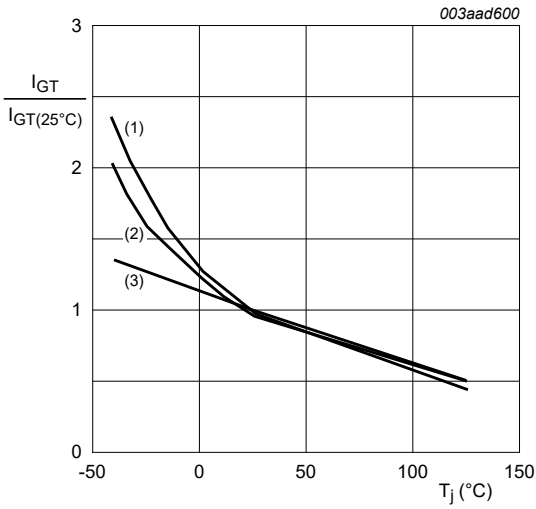
All dimensions are in mm

Fig. 8. Minimum footprint SOT223

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 9	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 9	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 9	-	-	10	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 10	-	-	12	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 10	-	-	18	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 10	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 11	-	-	12	mA
V _T	on-state voltage	I _T = 2 A; T _j = 25 °C; Fig. 12	-	0.7	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 13	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 13	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (67% of V _{DRM}); exponential waveform; gate open circuit	30	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit	2	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

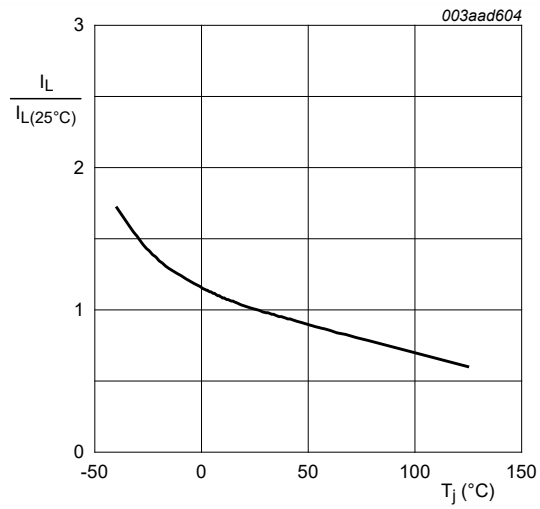


Fig. 10. Normalized latching current as a function of junction temperature

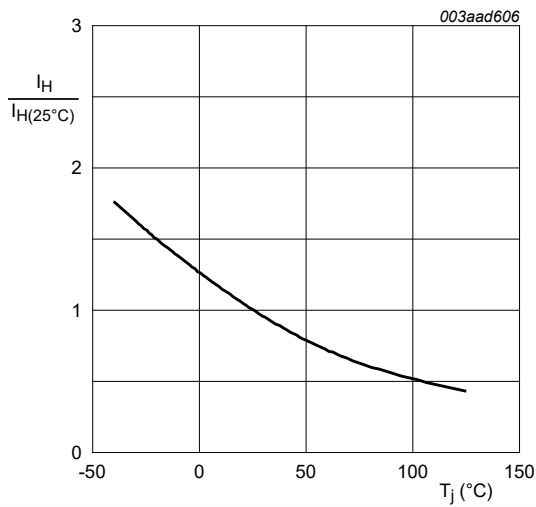
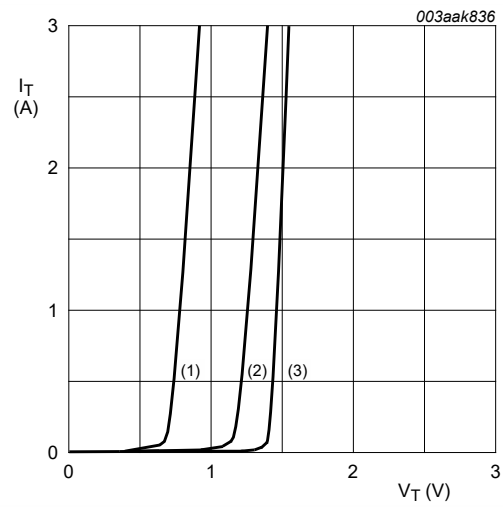


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$

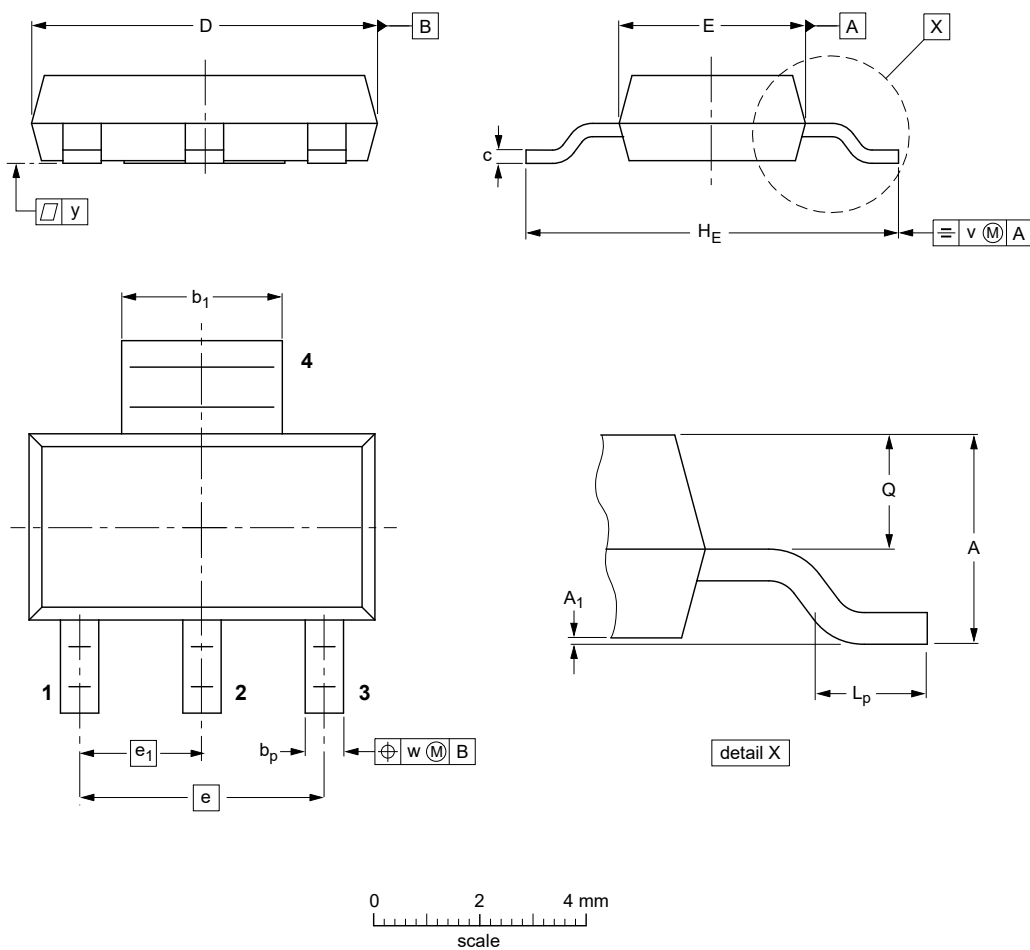
- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 12. On-state current as a function of on-state voltage

10. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

Fig. 14. Package outline SC-73 (SOT223)

IMPORTANT NOTICE – PLEASE READ CAREFULLY

SZGKT Microelectronics NV and its subsidiaries reserve the right to make changes, corrections, enhancements, modifications, and improvements to SZGKT.